

**Vishay Siliconix** 

RoHS

COMPLIANT

### Improved Quad CMOS Analog Switches

#### DESCRIPTION

The DG211B, DG212B analog switches are highly improved versions of the industry-standard DG211, DG212. These devices are fabricated in Vishay Siliconix' proprietary silicon gate CMOS process, resulting in lower on-resistance, lower leakage, higher speed, and lower power consumption.

These quad single-pole single-throw switches are designed for a wide variety of applications in telecommunications, instrumentation, process control, computer peripherals, etc. An improved charge injection compensation design minimizes switching transients. The DG211B and DG212B can handle up to  $\pm$  22 V, and have an improved continuous current rating of 30 mA. An epitaxial layer prevents latchup.

All devices feature true bi-directional performance in the on condition, and will block signals to the supply levels in the off condition.

The DG211B is a normally closed switch and the DG212B is a normally open switch. (see Truth Table.)

#### **FEATURES**

- ± 22 V supply voltage rating
- TTL and CMOS compatible logic
- Low on-resistance  $R_{DS(on)}$ : 50  $\Omega$
- Low leakage I<sub>D(on)</sub>: 20 pA
- Single supply operation possible
- Extended temperature range
- Fast switching t<sub>ON</sub>: 120 ns
- Low charge injection Q: 1 pC

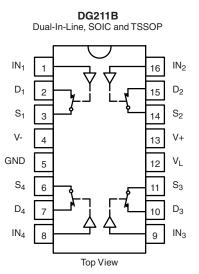
#### **BENEFITS**

- Wide analog signal range
- Simple logic interface
- Higher accuracy
- Minimum transients
- Reduced power consumption
- Superior to DG211, DG212
- Space savings (TSSOP)

#### **APPLICATIONS**

- Industrial instrumentation
- Test equipment
- Communications systems
- Disk drives
- Computer peripherals
- Portable instruments
- · Sample-and-hold circuits

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE				
Logic	DG211B	DG212B		
0	ON	OFF		
1	OFF	ON		

 $\begin{array}{l} \text{Logic "0"} \leq 0.8 \ \text{V} \\ \text{Logic "1"} \geq 2.4 \ \text{V} \end{array}$ 

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

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ORDERING INFORMATION						
Temp. Range	Package	Standard Part Number	Lead (Pb)-free Part Number			
	16-Pin Plastic DIP	DG211BDJ	DG211BDJ-E3			
		DG212BDJ	DG212BDJ-E3			
- 40 °C to 85 °C	16-Pin Narrow SOIC	DG211BDY DG211BDY-T1	DG211BDY-E3 DG211BDY-T1-E3			
		DG212BDY DG212BDY-T1	DG212BDY-E3 DG212BDY-T1-E3			
	16-Pin TSSOP	DG211BDQ DG211BDQ-T1	DG211BDQ-E3 DG211BDQ-T1-E3			
	10-riii 1330r	DG212BDQ DG212BDQ-T1	DG212BDQ-E3 DG212BDQ-T1-E3			

<b>ABSOLUTE MAXIMUM</b>	RATINGS (T <sub>A</sub> = 25 °C, unless oth	nerwise noted)			
Parameter		Limit	Unit		
Voltages Referenced, V+ to V-		44			
GND		25	v		
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first			
Current (Any terminal)		30	m 4		
Peak Current, S or D (Pulsed at 1	ms, 10 % duty cycle max.)	100	— mA		
Storage Temperature		- 65 to 125	°C		
Power Dissipation (Package) <sup>b</sup>	16-Pin Plastic DIP <sup>c</sup>	470	mW		
	16-Pin Narrow SOIC and TSSOP <sup>d</sup>	640			

Notes:

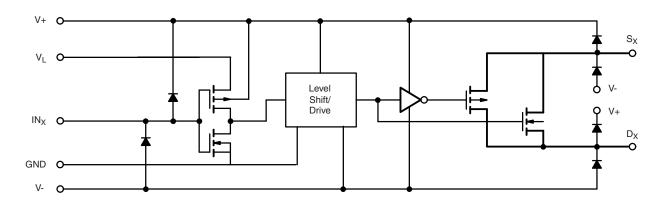
a. Signals on  $S_X$ ,  $D_X$ , or  $IN_X$  exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 6.5 mW/°C above 75 °C.

d. Derate 7.6 mW/°C above 75 °C.

#### SCHEMATIC DIAGRAM (Typical Channel)







# DG211B, DG212B Vishay Siliconix

SPECIFICATIONS							
		Test Conditions Unless Otherwise Specified		<b>D Suffix</b> - 40 °C to 85 °C			
Parameter	Symbol	$V_{+} = 15 V, V_{-} = -15 V$ $V_{L} = 5 V, V_{IN} = 2.4 V, 0.8 V^{e}$	Temp. <sup>a</sup>	Min. <sup>b</sup>	Typ. <sup>c</sup>	Max. <sup>b</sup>	Uni
Analog Switch				•	•	•	
Analog Signal Range <sup>d</sup>	V <sub>ANALOG</sub>		Full	- 15		15	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>D</sub> = ± 10 V, I <sub>S</sub> = 1 mA	Room Full		45	85 100	Ω
R <sub>DS(on)</sub> Match	$\Delta R_{DS(on)}$		Room		2		
Source Off Leakage Current	I <sub>S(off)</sub>	$V_{S} = \pm 14 \text{ V}, V_{D} = \pm 14 \text{ V}$	Room Full	- 0.5 - 5	± 0.01	0.5 5	
Drain Off Leakage Current	I <sub>D(off)</sub>	$V_D = \pm 14 \text{ V}, V_S = \pm 14 \text{ V}$	Room Full	- 0.5 - 5	± 0.01	0.5 5	nA
Drain On Leakage Current	I <sub>D(on)</sub>	$V_{S} = V_{D} = \pm 14 V$	Room Full	- 0.5 - 10	± 0.02	0.5 10	
Digital Control							
Input Voltage High	V <sub>INH</sub>		Full	2.4			v
Input Voltage Low	V <sub>INL</sub>		Full			0.8	v
Input Current	I <sub>INH</sub> or I <sub>INL</sub>	V <sub>INH</sub> or V <sub>INL</sub>	Full	- 1		1	μA
Input Capacitance	C <sub>IN</sub>		Room		5		pF
Dynamic Characteristics							
Turn-On Time	t <sub>ON</sub>	V <sub>S</sub> = 10 V	Room			300	-
Turn-Off Time	t <sub>OFF</sub>	see figure 2	Room			200	ns
Charge Injection	Q	$C_L$ = 1000 pF, $V_{gen}$ = 0 V, $R_{gen}$ = 0 $\Omega$	Room		1		pC
Source-Off Capacitance	C <sub>S(off)</sub>	V <sub>S</sub> = 0 V, f = 1 MHz	Room		5		
Drain-Off Capacitance	C <sub>D(off)</sub>	$v_{\rm S} = 0$ v, $i = 1$ MHz	Room		5		pF
Channel-On Capacitance	C <sub>D(on)</sub>	$V_D = V_S = 0 V$ , f = 1 MHz	Room		16		1
Off Isolation	OIRR	$C_{L} = 15 \text{ pF}, \text{ R}_{L} = 50 \Omega,$	Room		90		dB
Channel-to-Channel Crosstalk	X <sub>TALK</sub>	$V_{S} = 1 V_{RMS}$ , f = 100 kHz	Room		95		u
Power Supply							
Positive Supply Current	l+	V <sub>IN</sub> = 0 or 5 V	Room Full			10 50	
Negative Supply Current	I-	VIN - 0 01 5 V	Room Full	- 10 - 50			μA
Logic Supply Current	ΙL		Room Full			10 50	
Power Supply Range for Continuous Operation	V <sub>OP</sub>		Full	± 4.5		± 22	V

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SPECIFICATIONS (for Single Supply)							
		Test Conditions Unless Otherwise Specified		<b>D Suffix</b> - 40 °C to 85 °C			
Parameter	Symbol	V + = 12 V, V - = 0 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^e$	Temp. <sup>a</sup>	Min. <sup>b</sup>	Typ. <sup>c</sup>	Max. <sup>b</sup>	Unit
Analog Switch							
Analog Signal Range <sup>d</sup>	V <sub>ANALOG</sub>		Full	0		12	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	$V_{D} = 3 V, 8 V, I_{S} = 1 mA$	Room Full		90	160 200	Ω
Dynamic Characteristics			•				
Turn-On Time	t <sub>ON</sub>	V <sub>S</sub> = 8 V	Room			300	
Turn-Off Time	t <sub>OFF</sub>	see figure 1	Room			200	ns
Charge Injection	Q	$C_L = 1 \text{ nF}, V_{gen} = 6 \text{ V}, R_{gen} = 0 \Omega$	Room		4		рС
Power Supply			•				•
Positive Supply Current	l+		Room Full			10 50	
Negative Supply Current	I-	$V_{IN} = 0 \text{ or } 5 \text{ V}$	Room Full	- 10 - 50			μA
Logic Supply Current	ΙL		Room Full			10 50	
Power Supply Range for Continuous Operation	V <sub>OP</sub>		Full	+ 4.5		+ 25	V

Notes:

a. Room = 25 °C, Full = as determined by the operating temperature suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

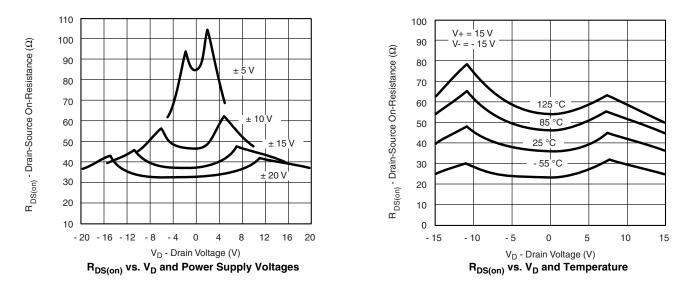
c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

d. Guaranteed by design, not subject to production test.

e. V<sub>IN</sub> = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

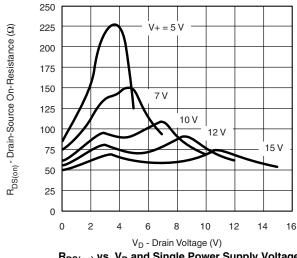
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



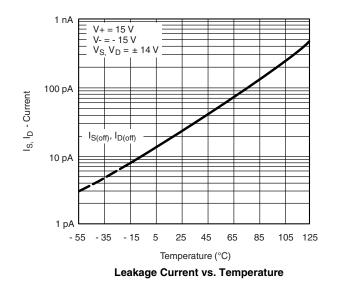


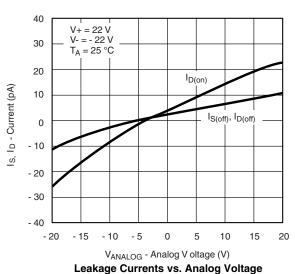
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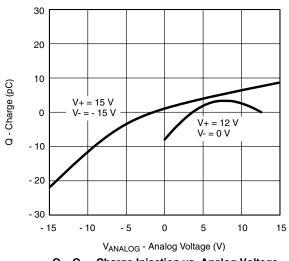
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



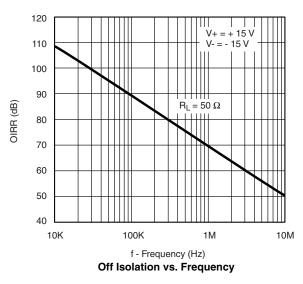








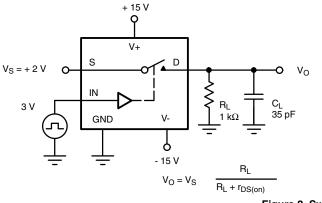
Q<sub>S</sub>, Q<sub>D</sub> - Charge Injection vs. Analog Voltage

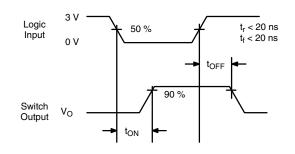


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### **TEST CIRCUITS**







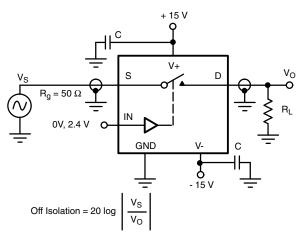


Figure 3. Off Isolation

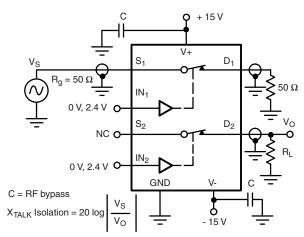
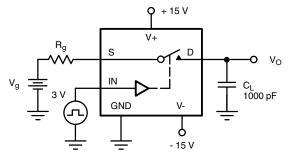
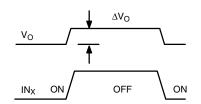


Figure 4. Channel-to-Channel Crosstalk





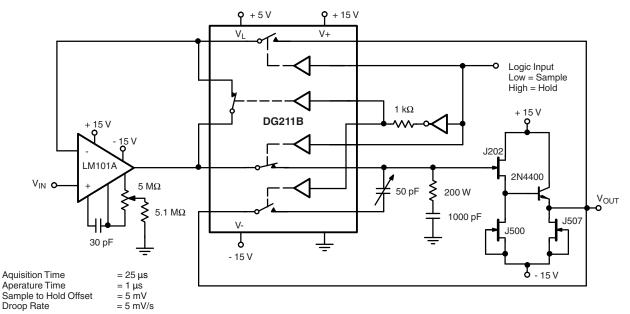
 $\Delta V_O$  = measured voltage error due to charge injection The charge injection in coulombs is Q = C\_L x  $\Delta V_O$ 

Figure 5. Charge Injection





#### **APPLICATIONS**





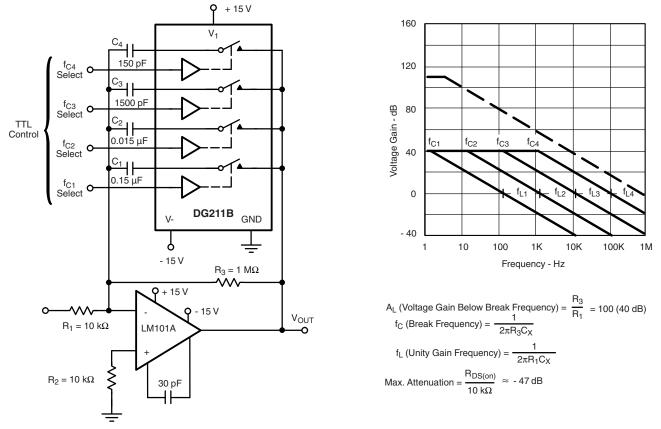


Figure 7. Active Low Pass Filter with Digitally Selected Break Frequency

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### APPLICATIONS

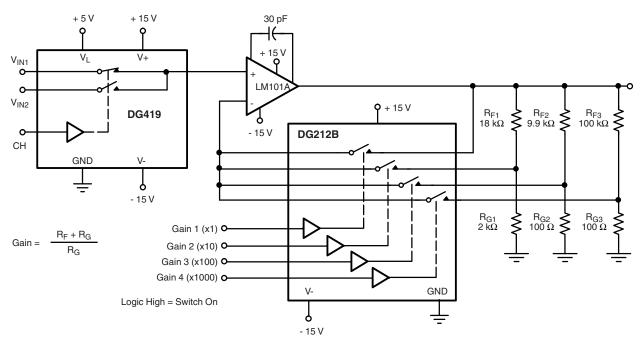


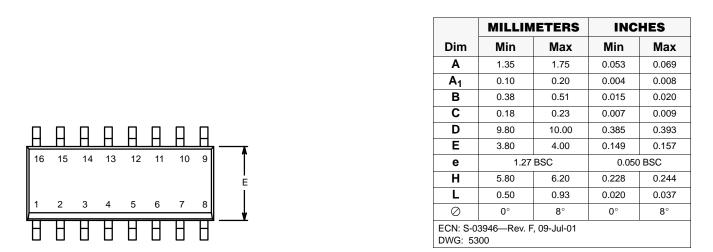
Figure 8. A Precision Amplifier with Digitally Programable Input and Gains

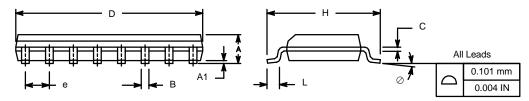
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?70040</u>.



SOIC (NARROW): 16-LEAD

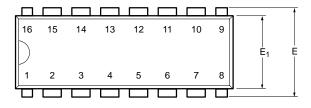
JEDEC Part Number: MS-012

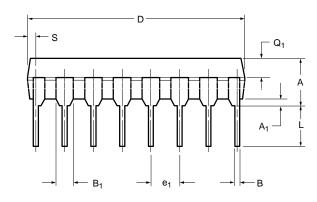


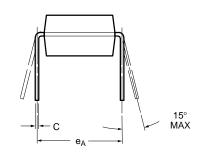




#### PDIP: 16-LEAD







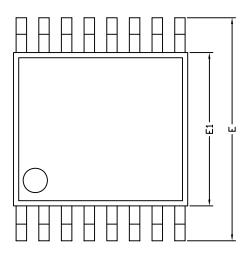
	MILLIN	IETERS	INC	HES	
Dim	Min	Max	Min	Max	
Α	3.81	5.08	0.150	0.200	
A <sub>1</sub>	0.38	1.27	0.015	0.050	
В	0.38	0.51	0.015	0.020	
B <sub>1</sub>	0.89	1.65	0.035	0.065	
С	0.20	0.30	0.008	0.012	
D	18.93	21.33	0.745	0.840	
E	7.62	8.26	0.300	0.325	
E <sub>1</sub>	5.59	7.11	0.220	0.280	
<b>e</b> <sub>1</sub>	2.29	2.79	0.090	0.110	
e <sub>A</sub>	7.37	7.87	0.290	0.310	
L	2.79	3.81	0.110	0.150	
Q <sub>1</sub>	1.27	2.03	0.050	0.080	
S	0.38	1.52	.015	0.060	
ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482					

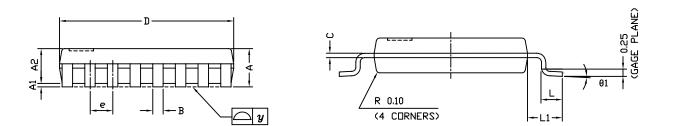


# Package Information

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### TSSOP: 16-LEAD





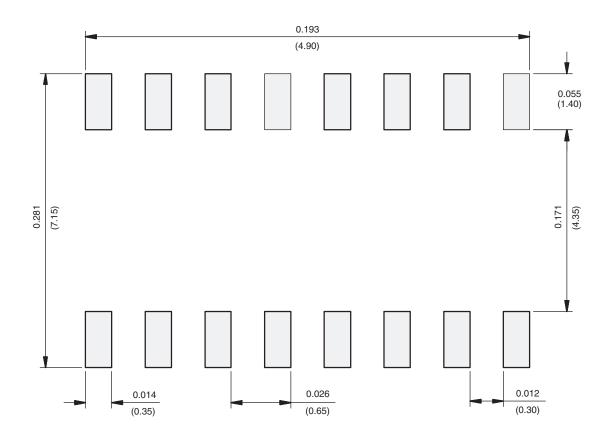
	DIMENSIONS IN MILLIMETERS				
Symbols	Min	Nom	Мах		
A	-	1.10	1.20		
A1	0.05	0.10	0.15		
A2	-	1.00	1.05		
В	0.22	0.28	0.38		
С	-	0.127	-		
D	4.90	5.00	5.10		
E	6.10	6.40	6.70		
E1	4.30	4.40	4.50		
е	-	0.65	-		
L	0.50	0.60	0.70		
L1	0.90	1.00	1.10		
у	-	-	0.10		
θ1	0°	3°	6°		
ECN: S-61920-Rev. D, 23-Oct-06 DWG: 5624					



**PAD** Pattern

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#### **RECOMMENDED MINIMUM PAD FOR TSSOP-16**



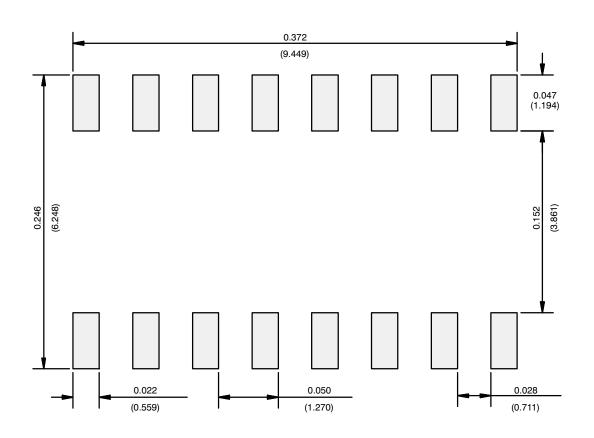
Recommended Minimum Pads Dimensions in inches (mm)

# **Application Note 826**

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#### **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

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